

ABSTRACT OF THE DISCLOSURE

[0035] In one embodiment, the invention generally provides a method for annealing a doped layer on a substrate including depositing a polycrystalline layer to a gate oxide layer and implanting the polycrystalline layer with a dopant to form a doped polycrystalline layer. The method further includes exposing the doped polycrystalline layer to a rapid thermal anneal to readily distribute the dopant throughout the polycrystalline layer. Subsequently, the method includes exposing the doped polycrystalline layer to a laser anneal to activate the dopant in an upper portion of the polycrystalline layer.